

NTE578 Silicon Rectifier Schottky Barrier, General Purpose

Description:

The NTE578 is a general purpose rectifier employing the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes, and polarity protection diodes.

Features:

- Low Reverse Current
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/High Efficiency
- Highly Stable Oxide Passivated Junction
- Guard-Ring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- High Surge Capacity

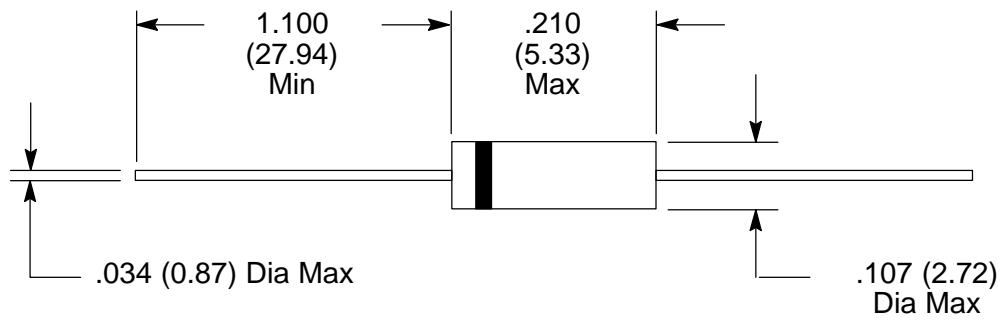
Absolute Maximum Ratings:

Peak Repetitive Reverse Voltage, V_{RRM} 90V
 Working Peak Reverse Voltage, V_{RWM} 90V
 DC Blocking Voltage, V_R 90V
 Average Rectified Forward Current, I_O
 (V_R (equiv) $\leq 0.2V_R$ (dc), $R_{\theta JA} = 50^\circ\text{C/W}$, P.C. Board Mounting, $T_A = +120^\circ\text{C}$) 1A
 Nonrepetitive Peak Surge Current, I_{FSM}
 (Surge applied at rated load conditions, half-wave single phase, 60Hz) 25A
 Operating Junction Temperature Range, T_J -65° to $+150^\circ\text{C}$
 Storage Temperature Range, T_{stg} -65° to $+150^\circ\text{C}$
 Voltage Rate of Change (Rated V_R), dv/dt 10V/ns
 Thermal Resistance, Junction-to-Ambient, R_{thJA} 1°C/W

Electrical Characteristics: ($T_L = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage	V_F	$I_F = 1\text{A}$, Note 1	–	–	0.6	V
Maximum Instantaneous Reverse Current	I_R	$V_R = 90\text{V}$, $T_L = +25^\circ\text{C}$	–	–	0.5	mA
		$V_R = 90\text{V}$, $T_L = +100^\circ\text{C}$	–	–	5.0	mA

Note 1. Pulse test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.



Color Band Denotes Cathode